

**SANYO**

No.1186D

**DSB015**

Silicon Epitaxial Planar Type

**High-Speed Switching Diode****Features**

- Ideally suited for use in hybrid ICs because of small-sized package
- Fast switching speed

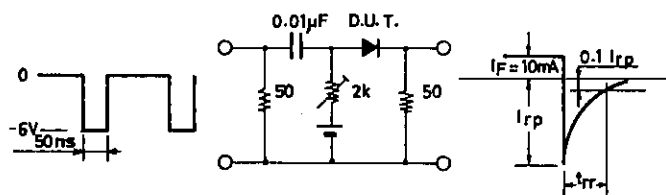
**Absolute Maximum Ratings at  $T_a = 25^\circ\text{C}$** 

|                           |                                |             | unit             |
|---------------------------|--------------------------------|-------------|------------------|
| Peak Reverse Voltage      | $V_{RM}$                       | -75         | V                |
| Reverse Voltage           | $V_R$                          | -50         | V                |
| Surge Current             | $I_{FSM}$ (1 $\mu\text{sec}$ ) | 4           | A                |
| Average Rectified Current | $I_O$                          | 150         | mA               |
| Peak Forward Current      | $I_{FM}$                       | 300         | mA               |
| Junction Temperature      | $T_j$                          | 125         | $^\circ\text{C}$ |
| Storage Temperature       | $T_{stg}$                      | -55 to +125 | $^\circ\text{C}$ |

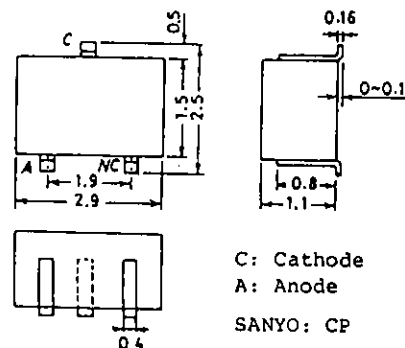
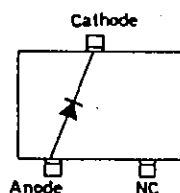
**Electrical Characteristics at  $T_a = 25^\circ\text{C}$** 

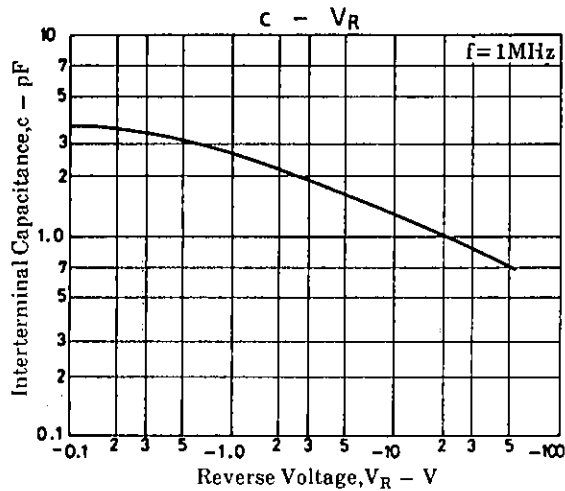
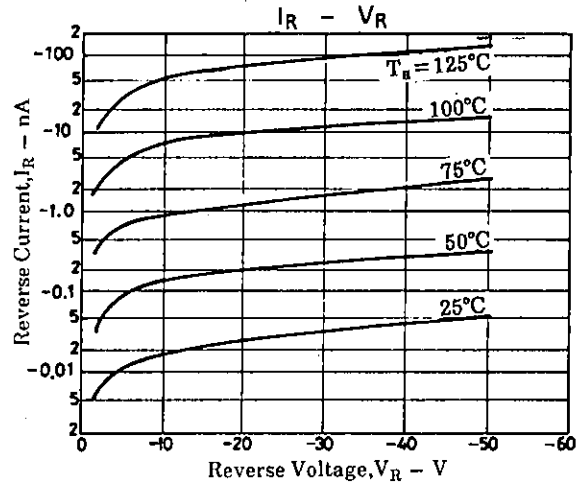
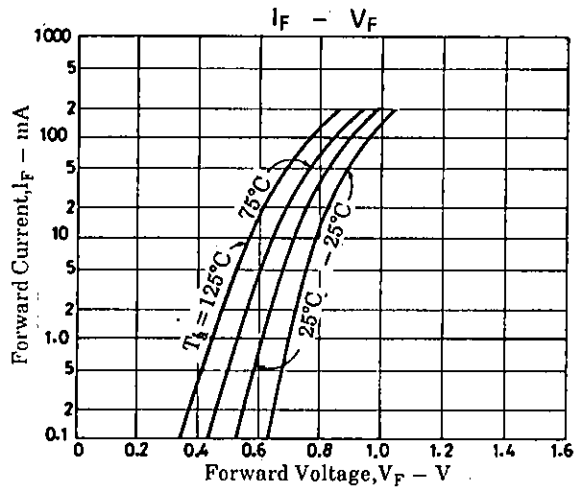
|                              |          |                                       | min | typ  | max | unit |
|------------------------------|----------|---------------------------------------|-----|------|-----|------|
| Forward Voltage              | $V_F$    | $I_F = 10\text{mA}$                   |     | 0.75 | 1.0 | V    |
|                              |          | $I_F = 50\text{mA}$                   |     | 0.85 | 1.0 | V    |
|                              |          | $I_F = 100\text{mA}$                  |     |      | 1.2 | V    |
| Reverse Current              | $I_R$    | $V_R = -50\text{V}$                   |     | -100 |     | nA   |
| Interterminal Capacitance    | $c$      | $V_R = 0\text{V}, f = 1\text{MHz}$    |     |      | 7   | pF   |
| Reverse Recovery Time        | $t_{rr}$ | $I_F = 10\text{mA}, V_R = -6\text{V}$ |     |      | 5   | ns   |
| Rated Input-Output Frequency |          | $R_L = 50\Omega, I_{rr} = 0.1I_{rp}$  |     |      | 20  | MHz  |

Marking : A2

**Reverse Recovery Time Test Circuit**

Unit (capacitance: F)

**Package Dimensions 1148**  
(unit: mm)**Electrical Connection**



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